

NPN Darlington transistor

PXTA14

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 30 V).

APPLICATIONS

- High input impedance preamplifiers.

DESCRIPTION

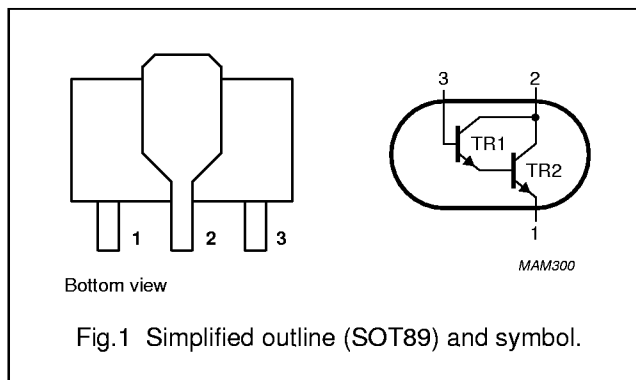
NPN Darlington transistor in a SOT89 plastic package.
PNP complement: PXTA64.

MARKING

TYPE NUMBER	MARKING CODE
PXTA14	p1N

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	30	V
V_{CES}	collector-emitter voltage	$V_{BE} = 0$	—	30	V
V_{EBO}	emitter-base voltage	open collector	—	10	V
I_C	collector current (DC)		—	500	mA
I_{CM}	peak collector current		—	1	A
I_B	base current (DC)		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	1.3	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm². For other mounting conditions, see “Thermal considerations for the SOT89 in the General Part of associated Handbook”.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	96	K/W
$R_{th\ j-s}$	thermal resistance from junction to solder point		16	K/W

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see *"Thermal considerations for the SOT89 in the General Part of associated Handbook"*.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 30\text{ V}$	–	100	nA
I_{CES}	collector cut-off current	$V_{BE} = 0$; $V_{CE} = 30\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 10\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$; (see Fig.2)	10000	–	
		$I_C = 100\text{ mA}$; $V_{CE} = 5\text{ V}$; (see Fig.2)	20000	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}$; $I_B = 0.1\text{ mA}$	–	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 100\text{ mA}$; $I_B = 0.1\text{ mA}$	–	1.5	V
V_{BEon}	base-emitter on-state voltage	$I_C = 100\text{ mA}$; $V_{CE} = 5\text{ V}$	–	2	V
f_T	transition frequency	$I_C = 30\text{ mA}$; $V_{CE} = 5\text{ V}$; $f = 100\text{ MHz}$	125	–	MHz

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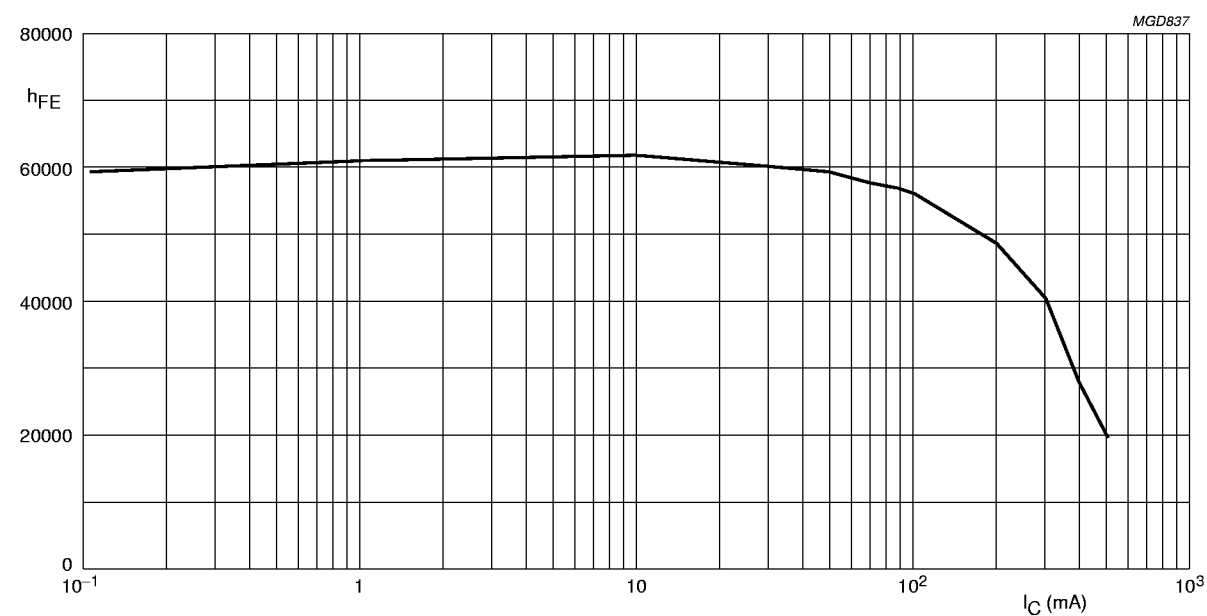


Fig.2 DC current gain; typical values.

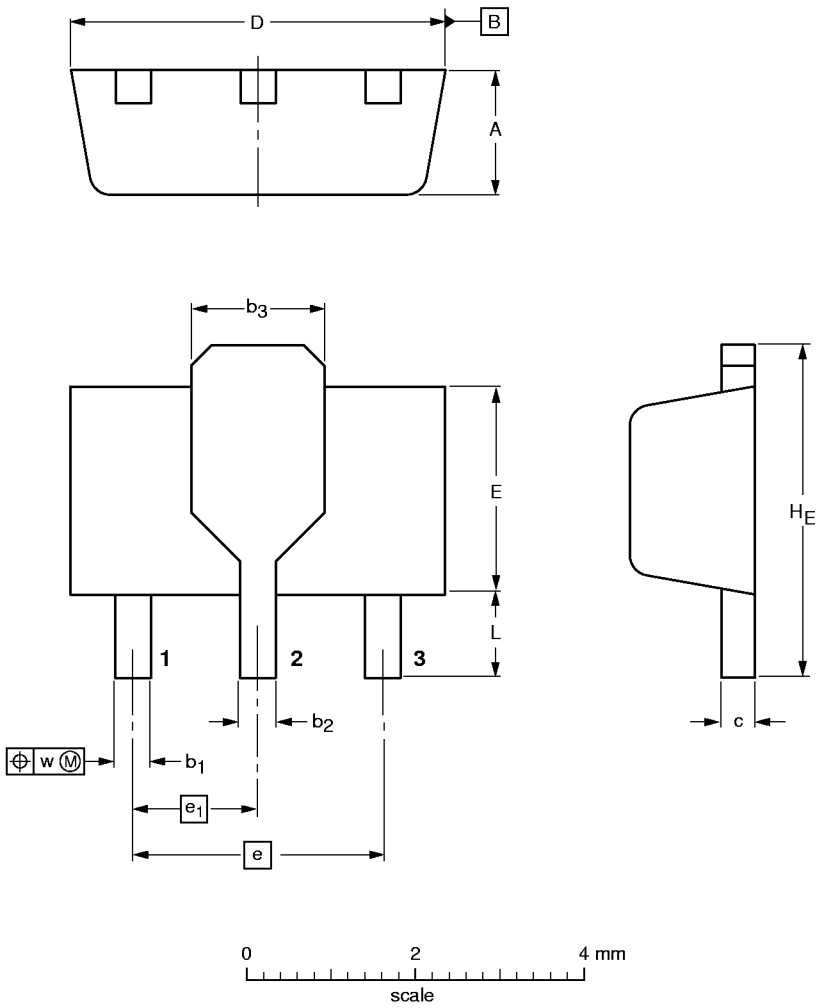
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b ₁	b ₂	b ₃	c	D	E	e	e ₁	H _E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89						97-02-28